Corrigendum to Commission Delegated Regulation (EU) 2019/2199 of 17 October 2019 amending Council Regulation (EC) No 428/2009 setting up a Community regime for the control of exports, transfer, brokering and transit of dual-use items

(Official Journal of the European Union of L 338 of 30 December 2019)

On page 129, point f is replaced as follows:

'f. Lithography equipment as follows:

1. Align and expose step and repeat (direct step on wafer) or step and scan (scanner) equipment for wafer processing using photo-optical or X-ray methods and having any of the following:
   a. A light source wavelength shorter than 193 nm; or
   b. Capable of producing a pattern with a "Minimum Resolvable Feature size" (MRF) of 45 nm or less;

   Technical Note:

   The "Minimum Resolvable Feature size" (MRF) is calculated by the following formula:

$$MRF = \frac{\text{(an exposure light source wavelength in nm) x (K factor)}}{\text{numerical aperture}}$$

   w.tifhere the K factor = 0,35
2. Imprint lithography equipment capable of producing features of 45 nm or less;

   Note: 3B001.f.2. includes:
   - *Micro contact printing tools*
   - *Hot embossing tools*
   - *Nano-imprint lithography tools*
   - *Step and flash imprint lithography (S-FIL) tools*
3. Equipment specially designed for mask making having all of the following:
   a. A deflected focussed electron beam, ion beam or "laser" beam; and
   b. Having any of the following:
      1. A full-width half-maximum (FWHM) spot size smaller than 65 nm and an image placement less than 17 nm (mean + 3 sigma); or
      2. Not used;
      3. A second-layer overlay error of less than 23 nm (mean + 3 sigma) on the mask;
4. Equipment designed for device processing using direct writing methods, having all of the following:
   a. A deflected focused electron beam; and
   b. Having any of the following:
      1. A minimum beam size equal to or smaller than 15 nm; or
      2. An overlay error less than 27 nm (mean + 3 sigma);'